

GaAs LIGHT-EMITTING DIODE "PIGTAIL" 62017 (TYPE GS 3040)



* HIGH INTENSITY GaAlAs VERSION AVAILABLE

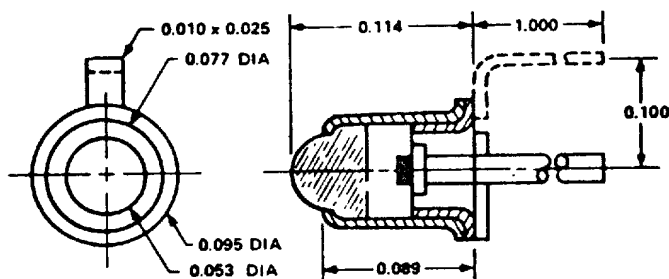
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MINIATURE HIGH EFFICIENCY LED WITH NARROW BEAM ANGLE
GLASS/METAL WELDED PACKAGE

Mii 62017 is a P-N GaAs Infrared Light Emitting Diode in a lensed coaxial package designed to be mounted in a single-clad printed circuit board. Its narrow beam angle and small size make it ideal for use in optical encoders, card reader arrays, etc.

This device is also available with a lead attached to the case so that it may be connected without the use of a printed board. Available screened to MIL-S-19500.

PHYSICAL DESCRIPTION



OPTICAL/ELECTRICAL CHARACTERISTICS AT 25°C

PARAMETER	OPTICAL POWER		FORWARD DROP	REVERSE BREAKDOWN	RADIATION RISE TIME	PEAK WAVELENGTH	BEAM ANGLE	FWD CURRENT CONTINUOUS
TEST CONDITION	$I_F = 50 \text{ mA}$		$I_F = 50 \text{ mA}$	$I_R = 10 \mu\text{A}$		$I_F = 50 \text{ mA}$	Note 1	25-C Case
SYMBOL	P_o		V_F	BV_R	t_r	λ_P	θ	I_F
UNIT	mW		VOLTS	VOLTS	μsec	nm	degrees	mA
	MIN	TYP	MAX	MIN	TYP	TYP	TYP	MAX
GS 3040-1	0.20	0.30	1.6	2.0	0.7	940	12	100
GS 3040-2	0.35	0.65	1.6	2.0	0.7	940	12	100
GS 3040-3	0.70	0.90	1.6	2.0	0.7	940	12	100
GS 3040-4	1.25	1.35	1.6	2.0	0.7	940	12	100

1 Angle between half intensity points

*contact factory

Ga As LIGHT-EMITTING DIODE, TYPE GS 3040, *Continued*

62017 LIGHT-EMITTING DIODE

ABSOLUTE MAXIMUM RATINGS 25°C FREE AIR TEMPERATURE UNLESS NOTED

Reverse Voltage at 25°C Case Temperature	2 V
Continuous Forward Current at 25°C Case Temperature (See Note)	100 mA
Operating Case Temperature Range	-55°C to 125°C
Storage Temperature Range	-55°C to 150°C
Soldering Temperature (3 Minutes)	240°C

NOTE: Derate linearly to 125°C free-air temperature at the rate of 1 mA/°C.

TYPICAL CHARACTERISTICS

